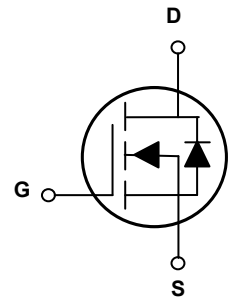
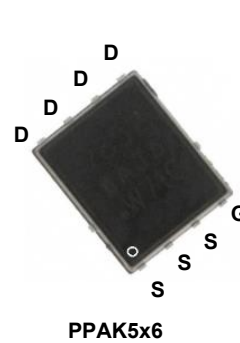


Main Product Characteristics

| | |
|--------------|---------------|
| BV_{DSS} | 80V |
| $R_{DS(ON)}$ | 3.6m Ω |
| I_D | 150A |



Schematic Diagram

Features and Benefits

- Advanced MOSFET process technology
- Ideal for high efficiency switched mode power supplies
- Low on-resistance with low gate charge
- Fast switching and reverse body recovery



Description

The GSFP08150 utilizes the latest techniques to achieve high cell density and low on-resistance. These features make this device extremely efficient and reliable for use in high efficiency switch mode power supplies and a wide variety of other applications.

Absolute Maximum Ratings ($T_C=25^\circ\text{C}$ unless otherwise specified)

| Parameter | Symbol | Max. | Unit |
|--|-----------------|-------------|---------------------------|
| Drain-Source Voltage | V_{DS} | 80 | V |
| Gate-Source Voltage | V_{GS} | ± 20 | V |
| Drain Current-Continuous ($T_C=25^\circ\text{C}$) | I_D | 150 | A |
| Drain Current-Continuous ($T_C=100^\circ\text{C}$) | | 96 | |
| Drain Current-Pulsed ¹ | I_{DM} | 600 | A |
| Single Pulse Avalanche Energy ² | E_{AS} | 520 | mJ |
| Single Pulse Avalanche Current ² | I_{AS} | 102 | A |
| Power Dissipation ($T_C=25^\circ\text{C}$) | P_D | 192 | W |
| Power Dissipation-Derate above 25°C | | 1.54 | |
| Thermal Resistance, Junction-to-Ambient | $R_{\theta JA}$ | 62 | $^\circ\text{C}/\text{W}$ |
| Thermal Resistance, Junction-to-Case | $R_{\theta JC}$ | 0.65 | $^\circ\text{C}/\text{W}$ |
| Operating Junction Temperature Range | T_J | -55 To +150 | $^\circ\text{C}$ |
| Storage Temperature Range | T_{STG} | -55 To +150 | $^\circ\text{C}$ |

Electrical Characteristics ($T_J=25^{\circ}\text{C}$ unless otherwise specified)

| Parameter | Symbol | Conditions | Min. | Typ. | Max. | Unit |
|---|--------------|---|------|------|-----------|------------|
| On / Off Characteristics | | | | | | |
| Drain-Source Breakdown Voltage | BV_{DSS} | $V_{GS}=0V, I_D=250\mu A$ | 80 | - | - | V |
| Drain-Source Leakage Current | I_{DSS} | $V_{DS}=80V, V_{GS}=0V, T_J=25^{\circ}\text{C}$ | - | - | 1 | μA |
| | | $V_{DS}=64V, V_{GS}=0V, T_J=85^{\circ}\text{C}$ | - | - | 10 | μA |
| Gate-Source Leakage Current | I_{GSS} | $V_{GS}=\pm 20V, V_{DS}=0V$ | - | - | ± 100 | nA |
| Static Drain-Source On-Resistance | $R_{DS(ON)}$ | $V_{GS}=10V, I_D=20A$ | - | 3 | 3.6 | m Ω |
| Gate Threshold Voltage | $V_{GS(th)}$ | $V_{GS}=V_{DS}, I_D=250\mu A$ | 2 | 3 | 4 | V |
| Forward Transconductance | g_{fs} | $V_{DS}=10V, I_D=3A$ | - | 14 | - | S |
| Dynamic and Switching Characteristics | | | | | | |
| Total Gate Charge ^{3,4} | Q_g | $V_{DS}=40V, I_D=75A, V_{GS}=10V$ | - | 68 | 100 | nC |
| Gate-Source Charge ^{3,4} | Q_{gs} | | - | 19 | 30 | |
| Gate-Drain Charge ^{3,4} | Q_{gd} | | - | 20 | 30 | |
| Turn-On Delay Time ^{3,4} | $t_{d(on)}$ | $V_{DD}=40V, R_G=6\Omega, V_{GS}=10V, I_D=75A$ | - | 30 | 45 | nS |
| Rise Time ^{3,4} | t_r | | - | 25 | 40 | |
| Turn-Off Delay Time ^{3,4} | $t_{d(off)}$ | | - | 45 | 70 | |
| Fall Time ^{3,4} | t_f | | - | 25 | 40 | |
| Input Capacitance | C_{iss} | $V_{DS}=40V, V_{GS}=0V, F=1\text{MHz}$ | - | 4600 | 6900 | pF |
| Output Capacitance | C_{oss} | | - | 990 | 1500 | |
| Reverse Transfer Capacitance | C_{rss} | | - | 16 | 24 | |
| Gate Resistance | R_g | $V_{GS}=0V, V_{DS}=0V, F=1\text{MHz}$ | - | 1.8 | - | Ω |
| Drain-Source Diode Characteristics and Maximum Ratings | | | | | | |
| Continuous Source Current | I_S | $V_G=V_D=0V,$ | - | - | 150 | A |
| Pulsed Source Current | I_{SM} | Force Current | - | - | 300 | A |
| Diode Forward Voltage | V_{SD} | $V_{GS}=0V, I_S=1A, T_J=25^{\circ}\text{C}$ | - | - | 1 | V |
| Reverse Recovery Time | t_{rr} | $V_R=50V, I_S=10A,$ | - | 70 | - | nS |
| Reverse Recovery Charge | Q_{rr} | $di/dt=100A/\mu s, T_J=25^{\circ}\text{C}$ | - | 160 | - | nC |

Note:

1. Repetitive rating: Pulsed width limited by maximum junction temperature.
2. $V_{DD}=50V, V_{GS}=10V, L=0.1\text{mH}, I_{AS}=102A, R_G=25\Omega,$ starting $T_J=25^{\circ}\text{C}$.
3. Pulse test: pulse width $\leq 300\mu s,$ duty cycle $\leq 2\%$.
4. Essentially independent of operating temperature.

Typical Electrical and Thermal Characteristic Curves

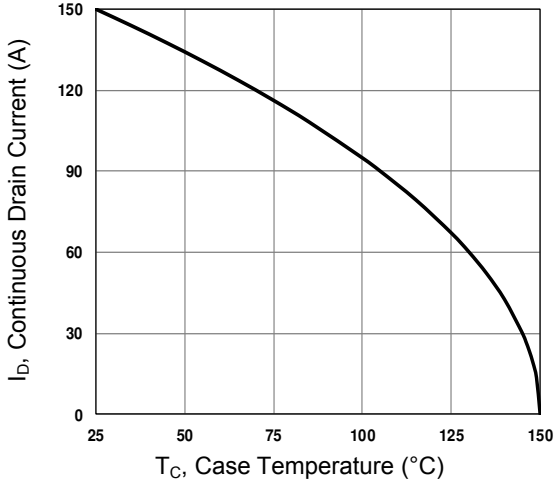


Figure 1. Continuous Drain Current vs. T_C

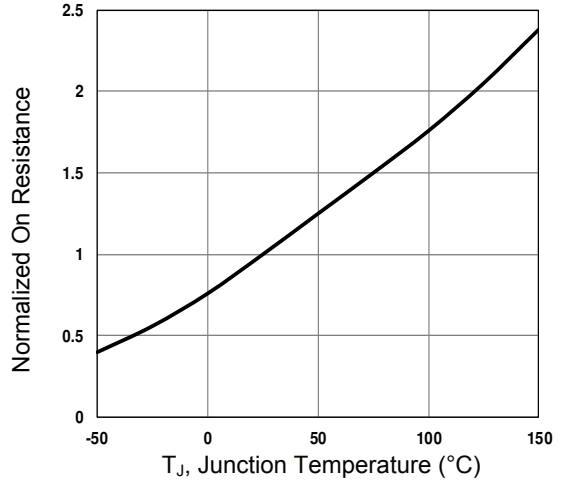


Figure 2. Normalized $R_{DS(on)}$ vs. T_J

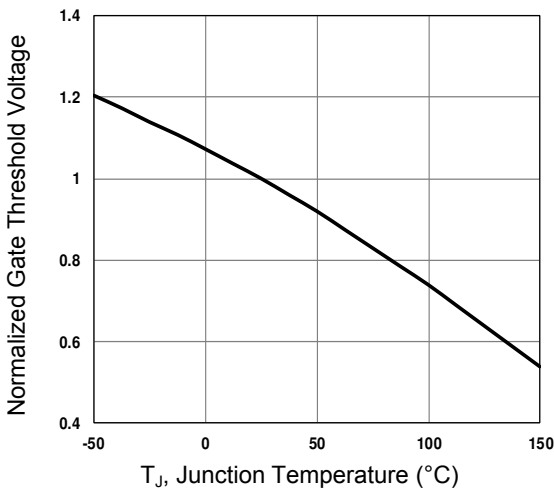


Figure 3. Normalized V_{th} vs. T_J

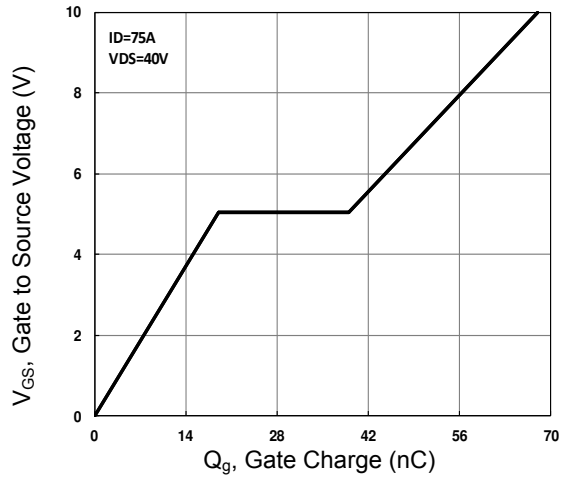


Figure 4. Gate Charge Characteristics

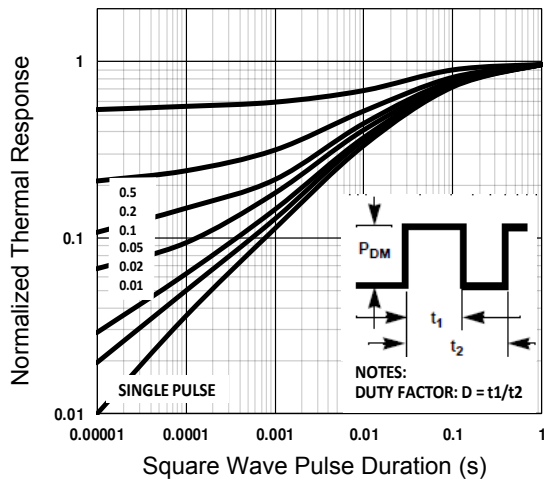


Figure 5. Normalized Transient Impedance

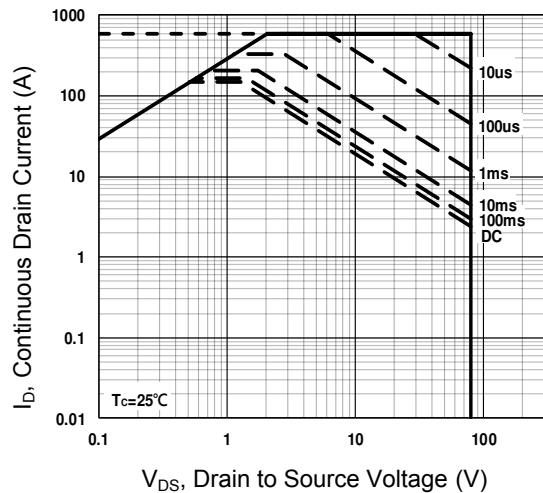


Figure 6. Maximum Safe Operation Area

Typical Electrical and Thermal Characteristic Curves

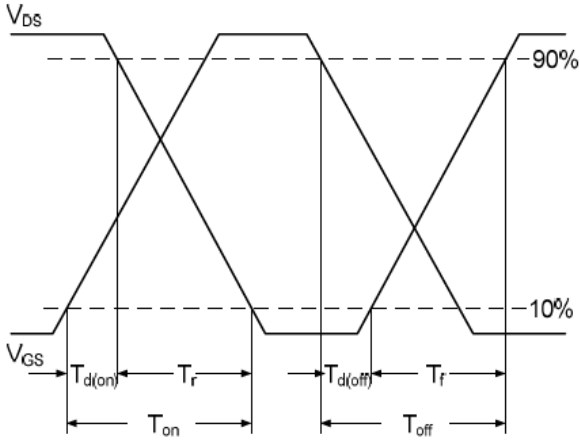


Figure 7. Switching Time Waveform

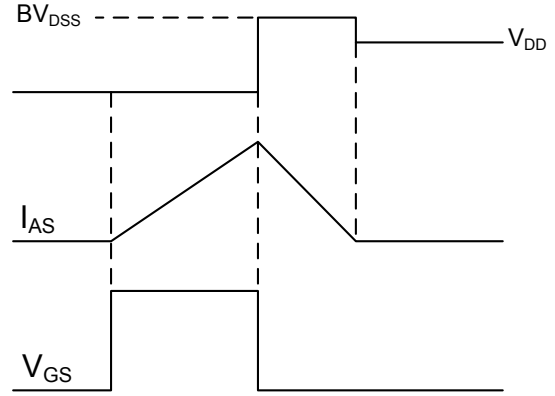
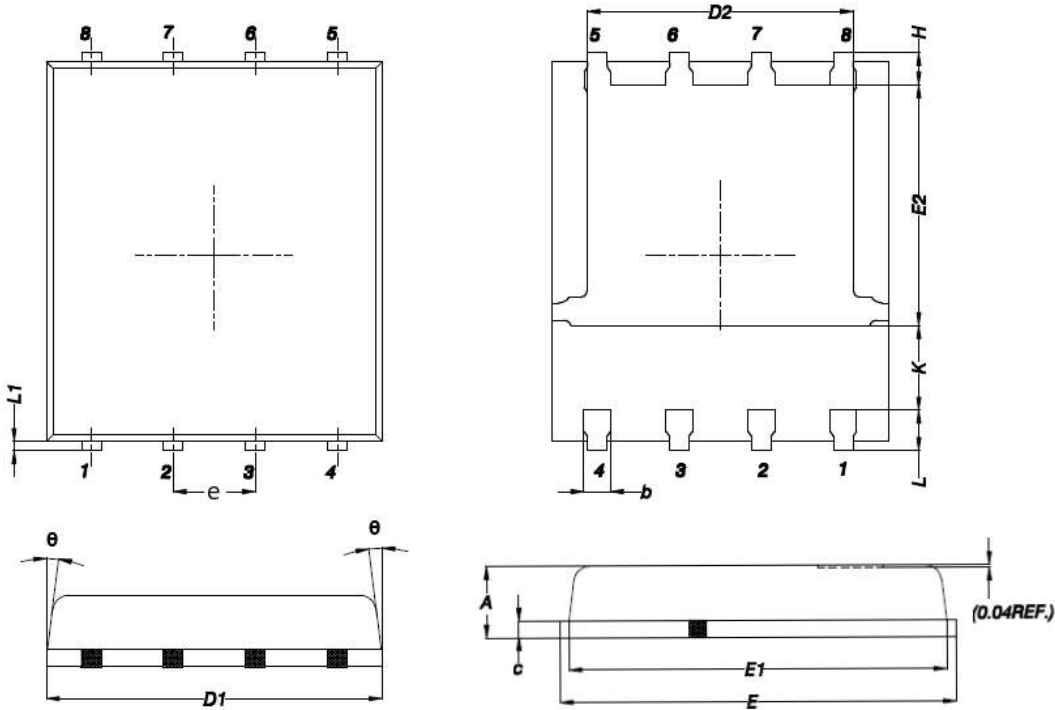


Figure 8. EAS Waveform

Package Outline Dimensions PPAK5x6



| Symbol | Dimensions in Millimeters | | Dimensions in Inches | |
|--------|---------------------------|-------|----------------------|-------|
| | Min | Max | Min | Max |
| A | 0.850 | 1.200 | 0.031 | 0.047 |
| b | 0.300 | 0.510 | 0.012 | 0.020 |
| C | 0.200 | 0.300 | 0.008 | 0.012 |
| D1 | 4.800 | 5.400 | 0.189 | 0.212 |
| D2 | 3.610 | 4.310 | 0.142 | 0.170 |
| E | 5.850 | 6.300 | 0.230 | 0.248 |
| E1 | 5.450 | 5.960 | 0.215 | 0.235 |
| E2 | 3.300 | 3.920 | 0.130 | 0.154 |
| e | 1.270 BSC | | 0.050 BSC | |
| H | 0.380 | 0.650 | 0.015 | 0.026 |
| K | 1.100 | - | 0.043 | - |
| L | 0.380 | 0.710 | 0.015 | 0.028 |
| L1 | 0.050 | 0.250 | 0.002 | 0.009 |
| θ | 0° | 12° | 0° | 12° |